

An Ultra-Low-Noise Differential Relaxation Oscillator based on a Swing-Boosting Scheme

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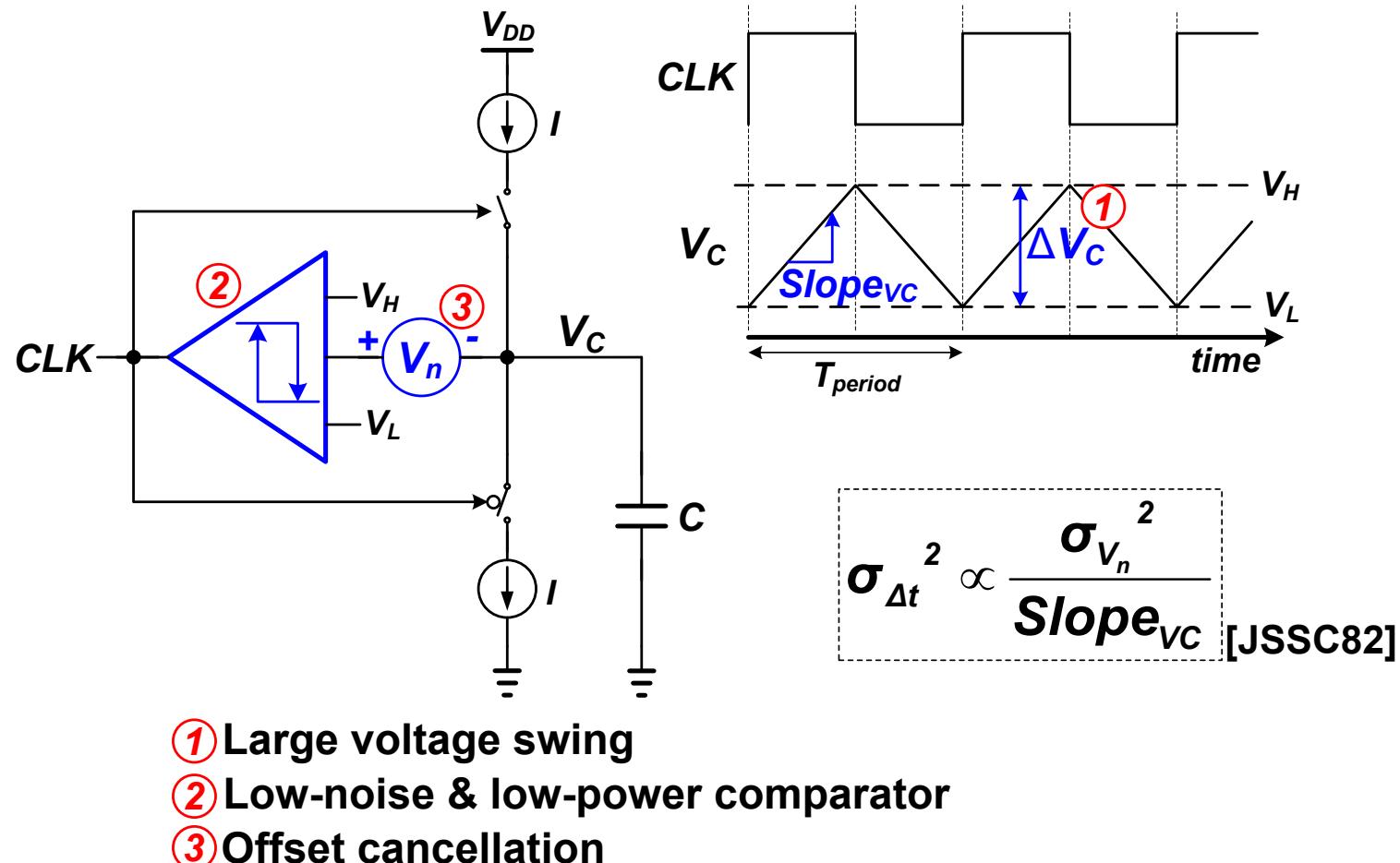
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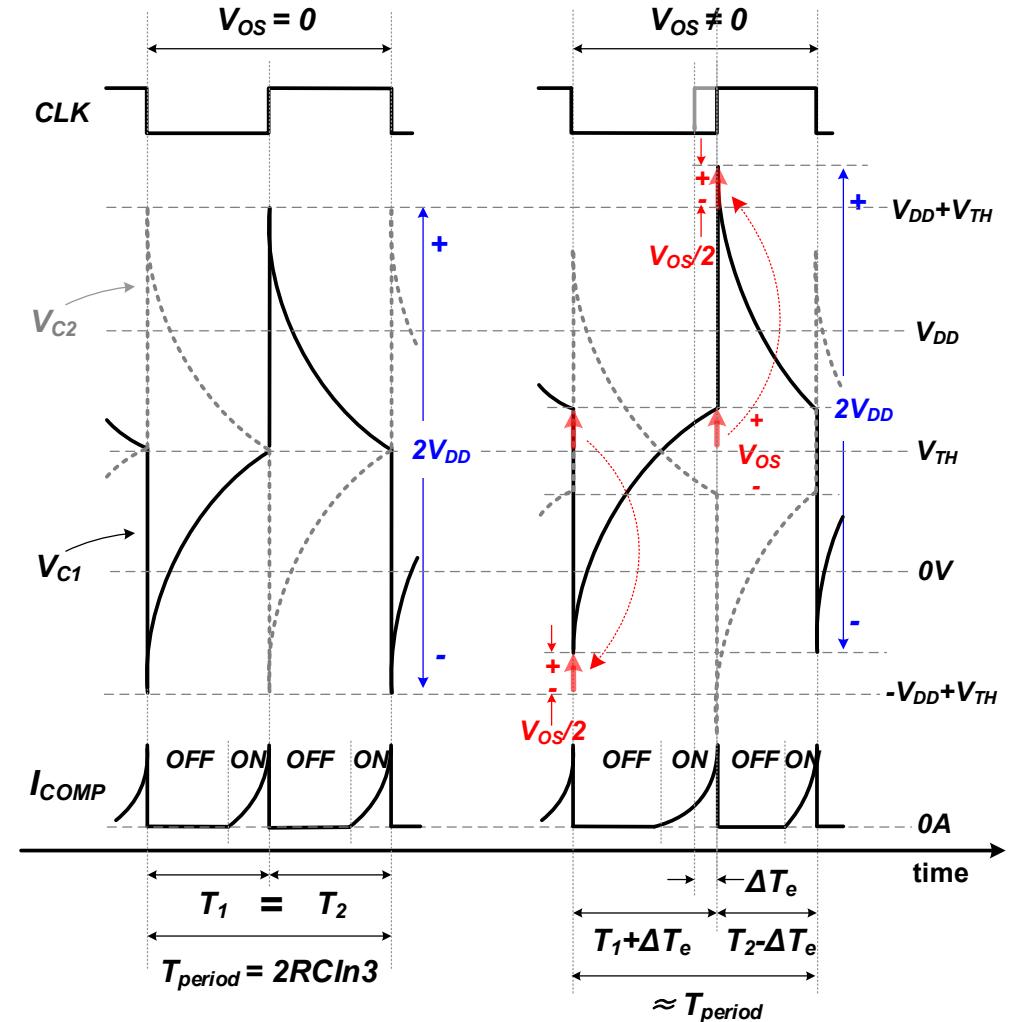
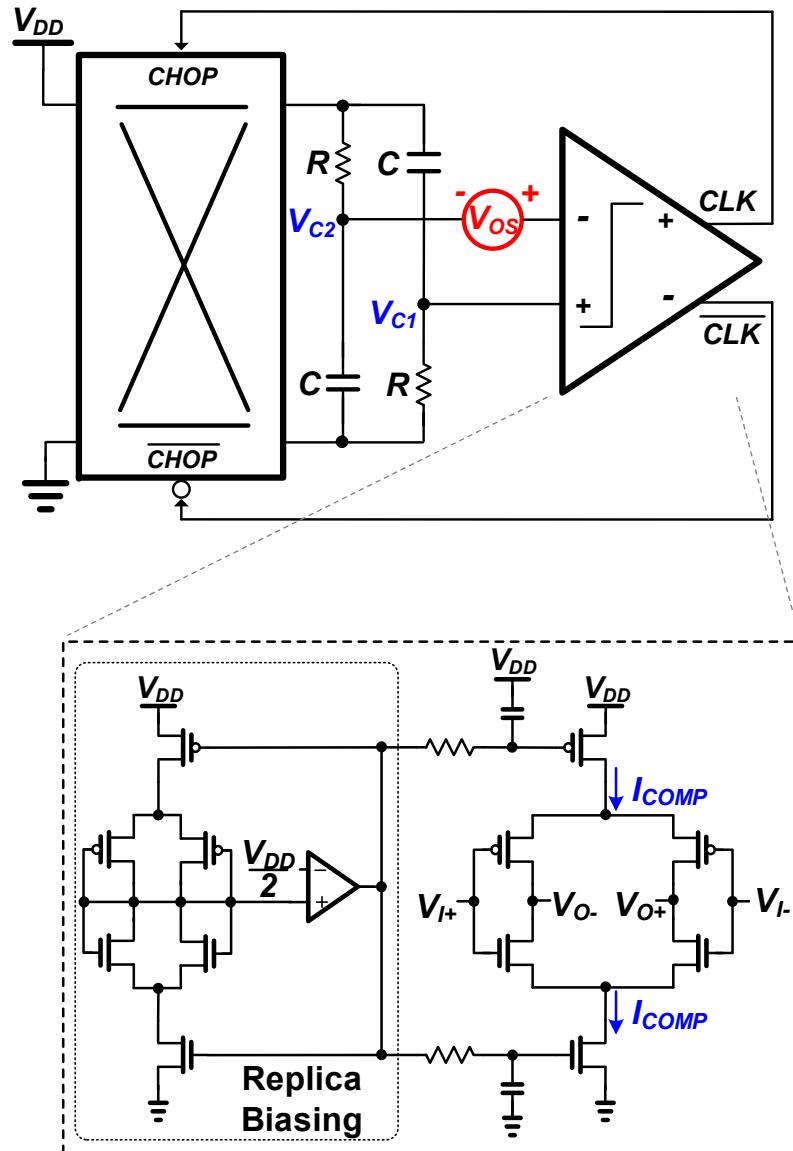
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Relaxation Oscillators

- Relaxation OSC: Low-power CLK ref, sensor front-ends for IoT
- Low FOM ($\sim 152.6\text{dB}$). Fundamental limit is 169.1dBc/Hz .
- Low-noise Design Considerations:



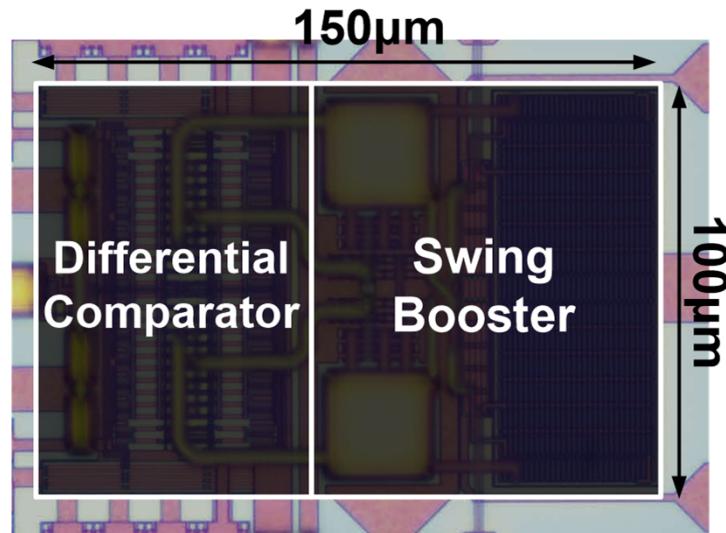
4A-1 Swing-boosted Differential Oscillator



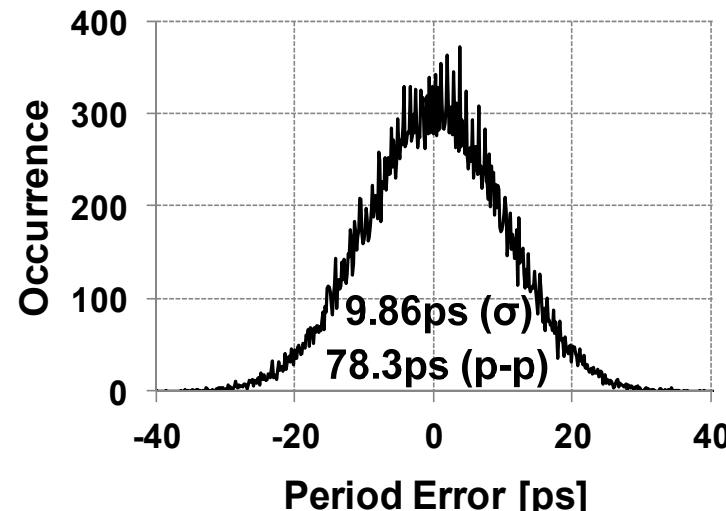
➤ Inherently resilient to offset and consumes dynamic power

4A-1

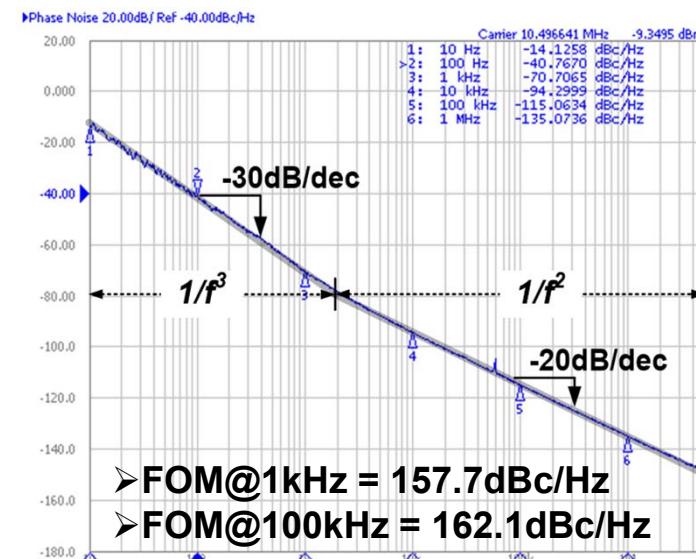
Measurement Results



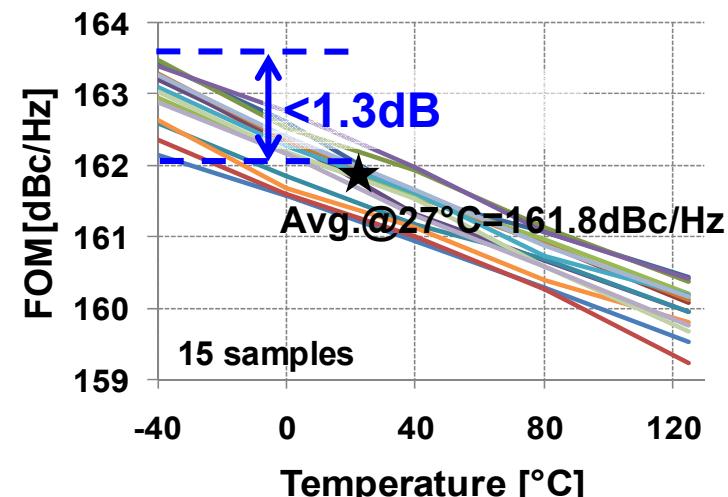
<Chip Micrograph>



<Jitter Measurement>



<Phase-noise Measurement>



<Robustness of Performance>

4A-1 Performance Summary & Conclusion

Parameters	ISSCC 08	ISSCC 09	VLSI 10	ISSCC 13	This Work
Technology [nm CMOS]	65	130	65	65	180
Approach	Anti-jitter technique	Autozeroing	Chopping-FLL	Chopping-FLL + Integrated error feedback	Differential swing boosting
Freq. [MHz]	12.5	3.2	6	12.6	10.5
Area [mm ²]	0.03	0.073	0.02	0.01	0.015
Min. V _{DD} [V]	1.3	1.4	1.15	1.1	1.4
Power [μ W]	91 ¹ / ~3600 ²	38	100	98.4	219.8
Period Jitter	N.A.	455ps _{rms} (0.146%)	88ps _{rms} (0.053%)	~55ps _{rms} (0.07%)	9.86ps _{rms} (0.01%)
FOM	162 @ 100kHz ¹ 148 @ 100kHz ²	132 @ 10kHz	137.6 @ 1kHz	154.1 @ 1kHz 152.6 @ 100kHz	157.7 @ 1kHz 162.1 @ 100kHz
Supply Var. [%/0.1V]	N.A.	0.4 @1.4 to 1.6V	0.26 @1.15 to 1.35V	0.0175 @1.1 to 1.5V	0.44 (Worst-case) @1.4 to 2V
Temp. Var. [ppm/°C]	N.A.	125 ³ @ 20 to 60°C	24 ⁴ @ -40 to 125°C	205 ³ @ 0 to 80°C	137 ³ (Worst-case) @ -40 to 125°C
Samples	1	1	1	1	15

¹Excludes power of anti-jitter comparator

²Includes power of anti-jitter comparator

³w/o temperature calibration, ⁴w/ temperature calibration

- Simple, small-area architecture achieving the highest FOM
- Easily extended to various low-power sensors